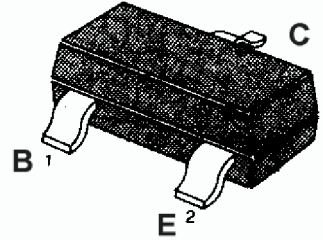


APPLICATION: Medium Power Amplifier Applications.

MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	40	V
Collector-emitter voltage	V _{CEO}	32	V
Emitter-base voltage	V _{EBO}	5	V
Collector current (DC)	I _C	800	mA
Collector current (Pulse)	I _C	1.5	A
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

SOT-23



1.Base 2.Emitter 3.Collector

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	120		390		V _{CE} = 3V, I _C = 100mA
Collector Cut-off Current	I _{CBO}			0.5	μA	V _{CB} = 20V, I _E =0
Emitter Cut-off Current	I _{EBO}			0.5	μA	V _{EB} = 4V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	40			V	I _C = 0.05mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	32			V	I _C = 1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	5			V	I _E = 0.05mA, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.4	V	I _C = 500mA, I _B = 50mA
Gain bandwidth product	f _T	100	150		MHz	I _C =50mA, V _{CE} =5V, f=100MHz
Common Base Output Capacitance	C _{ob}		10		pF	V _{CB} = 10V, I _E =0, f= 1MHz

h_{FE} Classification And Marking

Print Mark	81Q	81R
Classification	Q	R
h _{FE}	120~270	180~390